

Please amend the subject application as follows:

IN THE CLAIMS:

Please cancel claims 5-22 and 24 and accept amended claims 1 and 23 and new claims 25-26 as follows:

1. (currently amended) A capacitor comprising:
a lower electrode formed on a semiconductor substrate;
a dielectric film stacked on the lower electrode; and
an upper electrode formed on the dielectric film,
wherein the upper electrode is formed by chemical vapor deposition and physical vapor deposition, and the capacitor is a concave-type capacitor.
2. (original) The capacitor of claim 1, wherein the upper electrode is made of one selected from the group consisting of titanium nitride, tantalum nitride, tungsten nitride, ruthenium, platinum, iridium, and a combination thereof.
3. (original) The capacitor of claim 1, wherein the upper electrode includes a first upper electrode formed by the chemical vapor deposition and a second upper electrode formed by the physical vapor deposition and the first upper electrode and the second upper electrode are sequentially stacked.
4. (original) The capacitor of claim 1, wherein the upper electrode includes a first upper electrode formed by the physical vapor deposition and a second upper electrode formed by the chemical vapor deposition and the first upper electrode and the

second upper electrode are sequentially stacked.

5. - 22. (canceled)

23. (currently amended) A capacitor comprising:

a lower electrode formed on a semiconductor substrate;

a dielectric film stacked on the lower electrode; and

an upper electrode formed on the dielectric film,

wherein the upper electrode is formed by physical vapor deposition and one of chemical vapor deposition and atomic layer deposition, the upper electrode includes a first upper electrode and a second upper electrode and the capacitor is a concave-type capacitor.

24. (canceled)

25. (new) A capacitor comprising:

a lower electrode formed on a semiconductor substrate;

a dielectric film stacked on the lower electrode;

an upper electrode formed on the dielectric film, wherein the upper electrode is formed by chemical vapor deposition and physical vapor deposition, and includes a first upper electrode and a second upper electrode; and

an anti-reflective layer formed on the second upper electrode.

26. (new) The capacitor of claim 25, wherein the capacitor is a concave-type capacitor.